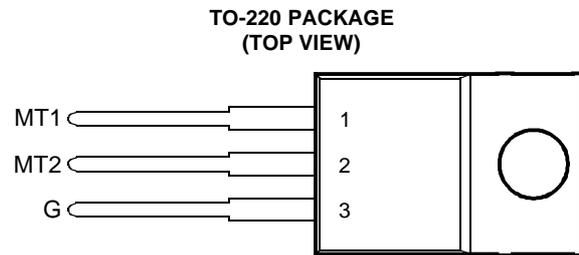


- Sensitive Gate Triacs
- 4 A RMS
- Glass Passivated Wafer
- 400 V to 800 V Off-State Voltage
- Max I_{GT} of 5 mA (Quadrants 1 - 3)



Pin 2 is in electrical contact with the mounting base.

MDC2ACA

absolute maximum ratings over operating case temperature (unless otherwise noted)

RATING		SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (see Note 1)	TIC206D	V_{DRM}	400	V
	TIC206M		600	
	TIC206S		700	
	TIC206N		800	
Full-cycle RMS on-state current at (or below) 85°C case temperature (see Note 2)		$I_{T(RMS)}$	4	A
Peak on-state surge current full-sine-wave (see Note 3)		I_{TSM}	25	A
Peak on-state surge current half-sine-wave (see Note 4)		I_{TSM}	30	A
Peak gate current		I_{GM}	±0.2	A
Peak gate power dissipation at (or below) 85°C case temperature (pulse width ≤ 200 μs)		P_{GM}	1.3	W
Average gate power dissipation at (or below) 85°C case temperature (see Note 5)		$P_{G(AV)}$	0.3	W
Operating case temperature range		T_C	-40 to +110	°C
Storage temperature range		T_{stg}	-40 to +125	°C
Lead temperature 1.6 mm from case for 10 seconds		T_L	230	°C

- NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
 2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 85°C derate linearly to 110°C case temperature at the rate of 160 mA/°C.
 3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
 4. This value applies for one 50-Hz half-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
 5. This value applies for a maximum averaging time of 20 ms.

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
I_{DRM} Repetitive peak off-state current	$V_D = \text{rated } V_{DRM}$	$I_G = 0$	$T_C = 110^\circ\text{C}$			±1	mA
I_{GTM} Peak gate trigger current	$V_{supply} = +12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		0.5	5	mA
	$V_{supply} = +12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-1.5	-5	
	$V_{supply} = -12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-2	-5	
	$V_{supply} = -12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		3.6	10	
V_{GTM} Peak gate trigger voltage	$V_{supply} = +12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		0.7	2	V
	$V_{supply} = +12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-0.7	-2	
	$V_{supply} = -12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-0.8	-2	
	$V_{supply} = -12\text{ V}^\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		0.8	2	

† All voltages are with respect to Main Terminal 1.

PRODUCT INFORMATION

Information is current as of publication date. Products conform to specifications in accordance with the terms of Power Innovations standard warranty. Production processing does not necessarily include testing of all parameters.

TIC206 SERIES SILICON TRIACS

DECEMBER 1971 - REVISED MARCH 1997

electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{TM} Peak on-state voltage	$I_{TM} = \pm 4.2$ A $I_G = 50$ mA (see Note 6)		± 1.3	± 2.2	V
I_H Holding current	$V_{supply} = +12$ V† $I_G = 0$ Init' $I_{TM} = 100$ mA $V_{supply} = -12$ V† $I_G = 0$ Init' $I_{TM} = -100$ mA		2 -4	15 -15	mA
I_L Latching current	$V_{supply} = +12$ V† (see Note 7) $V_{supply} = -12$ V†			30 -30	mA
dv/dt Critical rate of rise of off-state voltage	$V_{DRM} = \text{Rated } V_{DRM}$ $I_G = 0$ $T_C = 110^\circ\text{C}$		± 50		V/ μ s
dv/dt _(c) Critical rise of commutation voltage	$V_{DRM} = \text{Rated } V_{DRM}$ $I_{TRM} = \pm 4.2$ A $T_C = 85^\circ\text{C}$	± 1	± 1.3	± 2.5	V/ μ s

† All voltages are with respect to Main Terminal 1.

NOTES: 6. This parameter must be measured using pulse techniques, $t_p \leq 1$ ms, duty cycle $\leq 2\%$. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

7. The triacs are triggered by a 15-V (open circuit amplitude) pulse supplied by a generator with the following characteristics:
 $R_G = 100 \Omega$, $t_{p(g)} = 20 \mu\text{s}$, $t_r \leq 15$ ns, $f = 1$ kHz.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			7.8	$^\circ\text{C/W}$
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	$^\circ\text{C/W}$

TYPICAL CHARACTERISTICS

**GATE TRIGGER CURRENT
VS
TEMPERATURE**

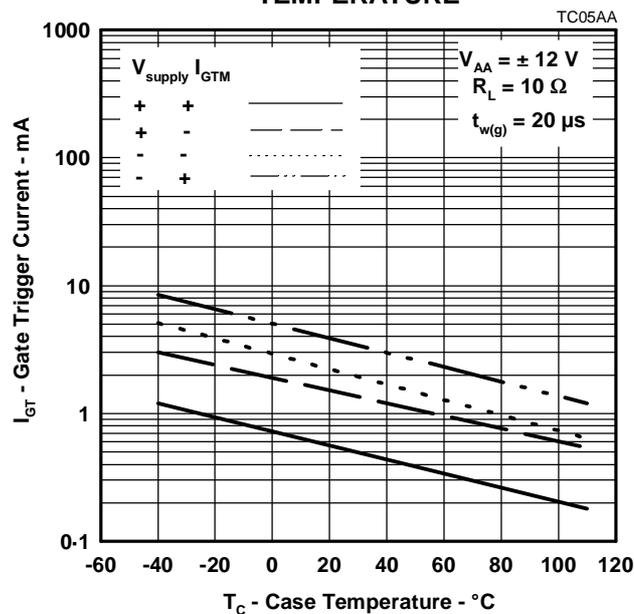


Figure 1.

**GATE TRIGGER VOLTAGE
VS
TEMPERATURE**

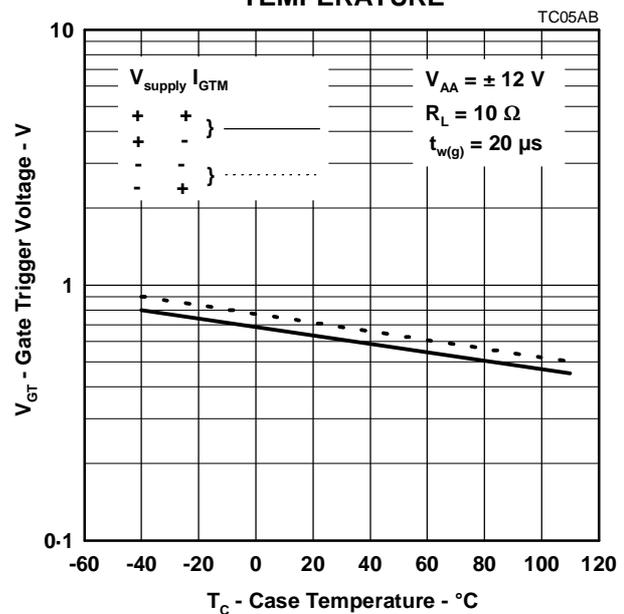


Figure 2.

TYPICAL CHARACTERISTICS

HOLDING CURRENT
VS
CASE TEMPERATURE

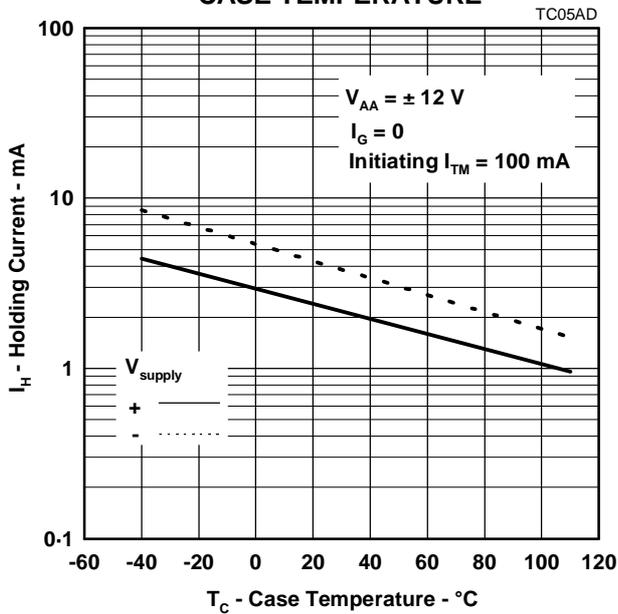


Figure 3.

GATE FORWARD VOLTAGE
VS
GATE FORWARD CURRENT

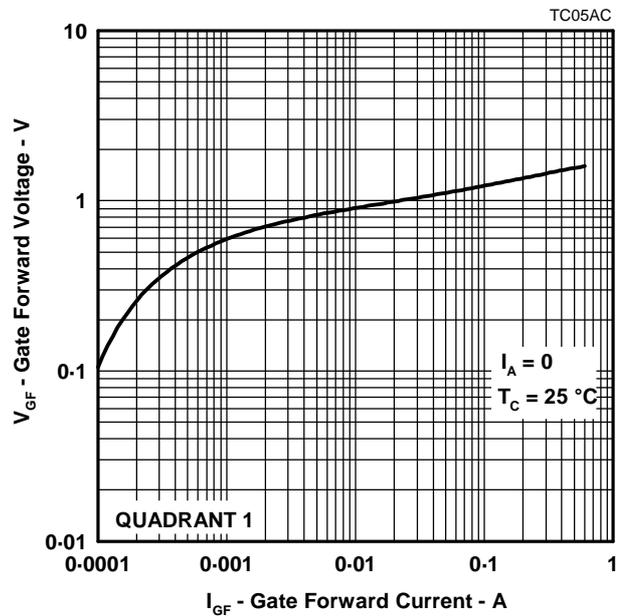


Figure 4.

LATCHING CURRENT
VS

CASE TEMPERATURE

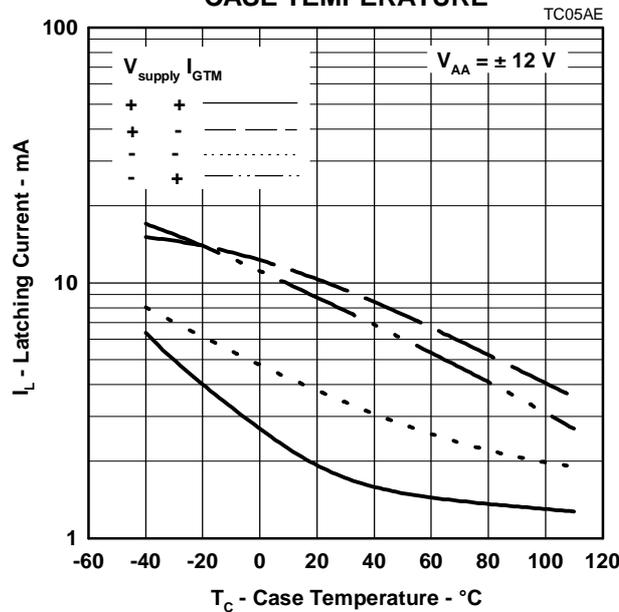


Figure 5.

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